IF1331

N-Channel Silicon Junction Field-Effect Transistor

- Low-Noise, High Gain Amplifier

Absolute maximum ratings at T_A = 25°C

Reverse Gate Source & Reverse Gate Drain Voltage	– 20 V
Continuous Forward Gate Current	10 mA
Continuous Device Power Dissipation	225 mW
Power Derating	1.8 mW/°C
Storage Temperature Range	– 65°C to 200°C

At 25°C free air temperature:		IF1331		Process NJ132H		
Static Electrical Characteristics		**Min**	**Max**	**Unit**	**Test Conditions**	
Gate Source Breakdown Voltage	$V_{(BR)GSS}$	– 20		V	I_G = – 1 µA, V_{DS} = ØV	
Gate Reverse Current	I_{GSS}		– 0.1	nA	V_{DS} = ØV, V_{GS} = – 10V	
Gate Source Cutoff Voltage	$V_{GS(OFF)}$	– 0.35	– 1.5	V	V_{DS} = 10V, I_D = 0.5 nA	
Drain Saturation Current (Pulsed)	I_{DSS}	5	20	mA	V_{DS} = 10V, V_{GS} = ØV	
Dynamic Electrical Characteristics						
Common Source Forward Transconductance	g_{fs}	10		mS	V_{DS} = 10V, I_D = 5 mA	f = 1 kHz
Common Source Input Capacitance	C_{iss}		20	pF	V_{DS} = 10V, I_D = 5 mA	f = 1 MHz
Common Source Reverse Transfer Capacitance	C_{rss}		5	pF	V_{DS} = 10V, I_D = 5 mA	f = 1 MHz
		Typ				
Equivalent Short Circuit Input Noise Voltage	$\bar{e}_N$	2.5		nV/√Hz	V_{DS} = 10V, I_D = 5 mA	f = 1 kHz

TO-72 Package
Dimensions in Inches (mm)

Pin Configuration
1 Source, 2 Drain, 3 Gate, 4 Case

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